

TO-252 N Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

■Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=26m\Omega(\text{Type})@V_{GS}=10V$

$R_{DS(ON)}=33m\Omega(\text{Type})@V_{GS}=4.5V$

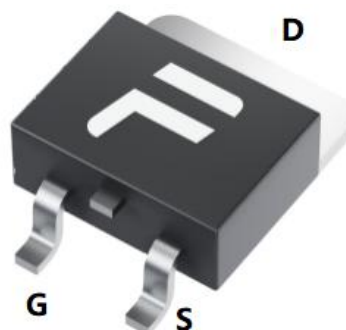
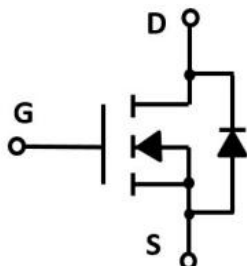
■Applications 应用

Load switch 负载开关

DC/DC Converter 升压转换

Power Management 电源管理

■Internal Schematic Diagram 内部结构



■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	60	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_C = 25^\circ C$)	20	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	80	A
Total Device Dissipation 总耗散功率	$P_D(\text{at } T_C = 25^\circ C)$	27.7	W
Thermal Resistance Junction-Ambient/Case 热阻	$R_{\theta JA}/R_{\theta JC}$	62/5.4	$^\circ C/W$
Avalanche Energy Single Pulse 雪崩能量	E_{AS}	18	mJ
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~175	$^\circ C$

■ Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	60	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	1	—	2.5	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =60V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V _{GS} =+20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =10A, V _{GS} =10V) (I _D =5A, V _{GS} =4.5V)	R _{DS(ON)}	—	26 33	33 45	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} =20A, V _{GS} =0V)	V _{SD}	—	—	1.2	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =25V, f=1MHz)	C _{ISS}	—	1148	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =25V, f=1MHz)	C _{OSS}	—	58.5	—	pF
Reverse Transfer Capacitance 反馈电容 (V _{GS} =0V, V _{DS} =25V, f=1MHz)	C _{RSS}	—	49.4	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _g	—	20.3	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _{gs}	—	3.7	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =30V, I _D =10A, V _{GS} =10V)	Q _{gd}	—	5.3	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =30V I _D =20A, R _{GEN} =1.8Ω, V _{GS} =10V)	t _{d(on)}	—	7.6	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =30V I _D =20A, R _{GEN} =1.8Ω, V _{GS} =10V)	t _r	—	20	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =30V I _D =20A, R _{GEN} =1.8Ω, V _{GS} =10V)	t _{d(off)}	—	15	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =30V I _D =20A, R _{GEN} =1.8Ω, V _{GS} =10V)	t _f	—	24	—	ns

■ Typical Characteristic Curve 典型特性曲线

Figure1: Output Characteristics

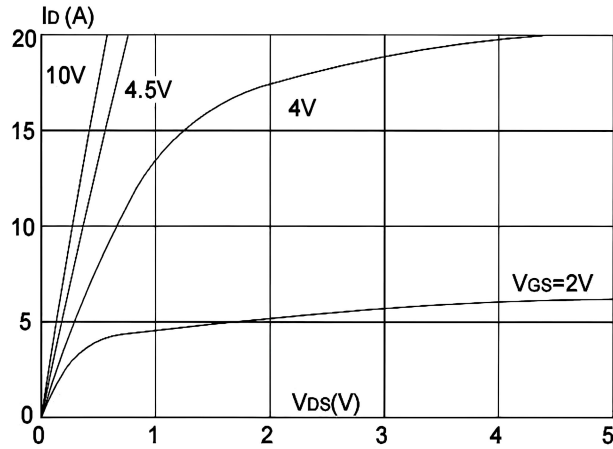


Figure 2: Typical Transfer Characteristics

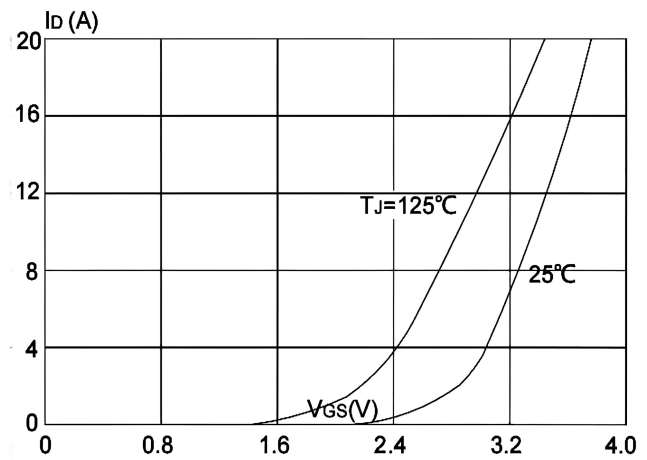


Figure 3: On-resistance vs. Drain Current

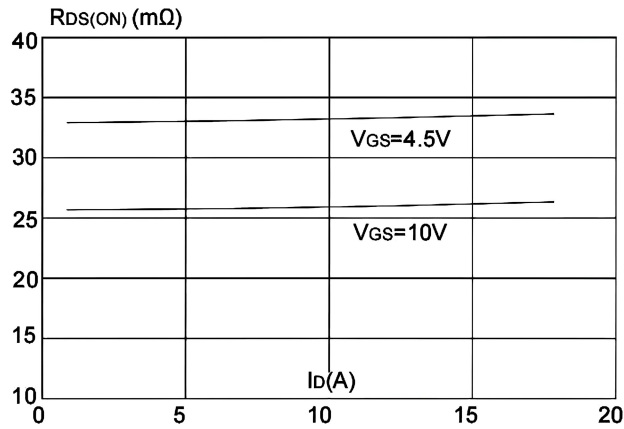


Figure 4: Body Diode Characteristics

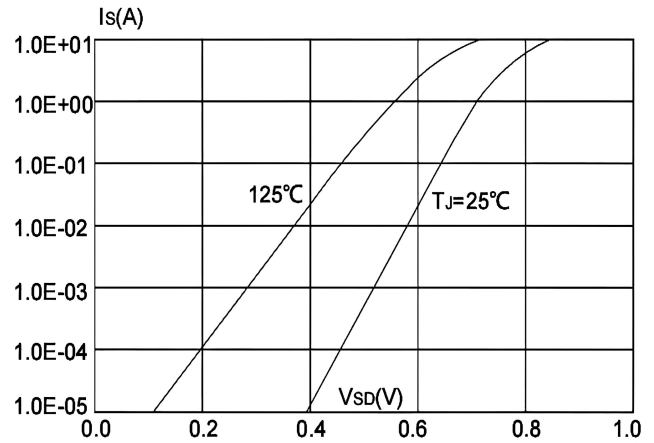


Figure 5: Gate Charge Characteristics

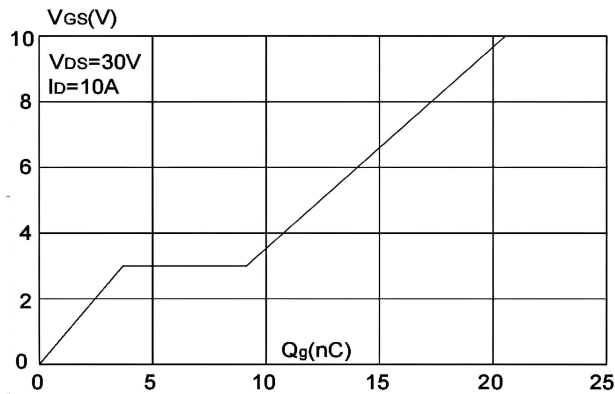
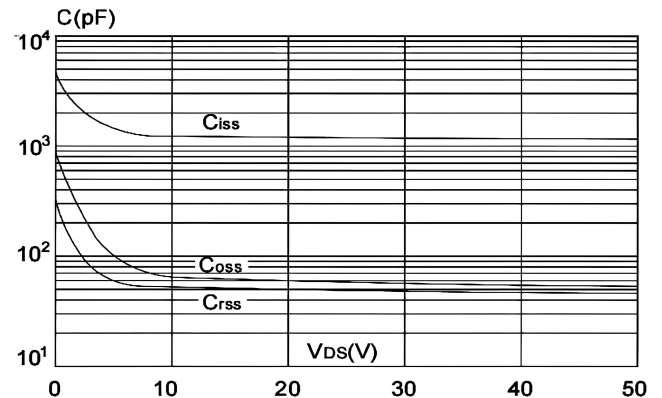


Figure 6: Capacitance Characteristics



■ Typical Characteristic Curve 典型特性曲线

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

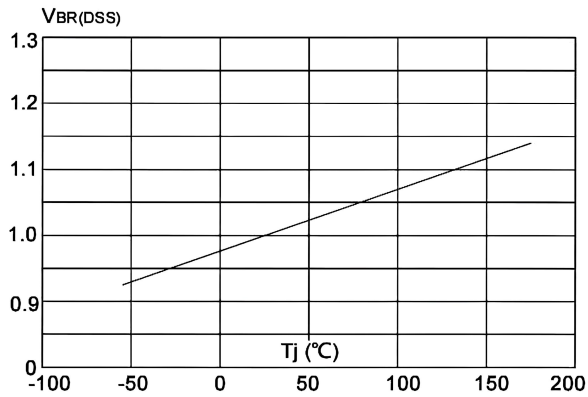


Figure 8: Normalized on Resistance vs. Junction Temperature

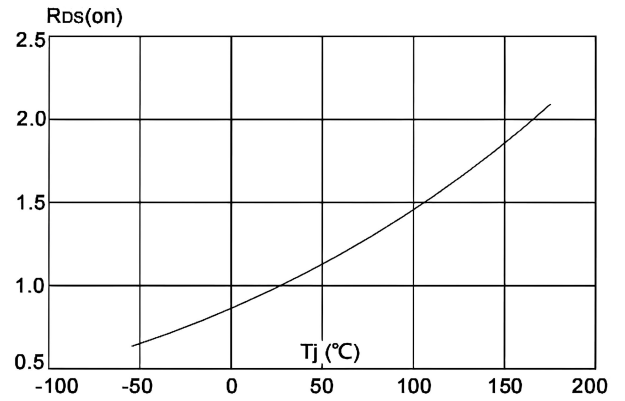


Figure 9: Maximum Safe Operating Area

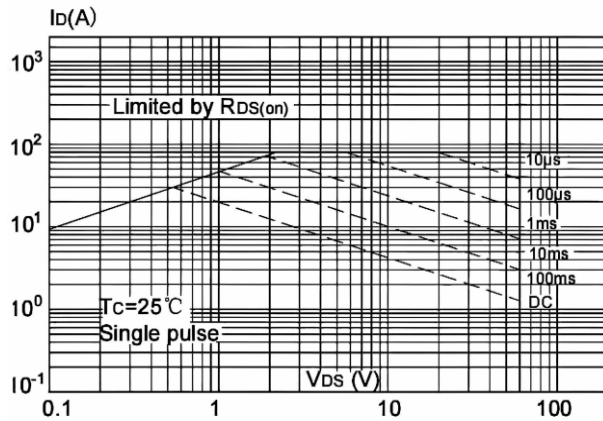


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

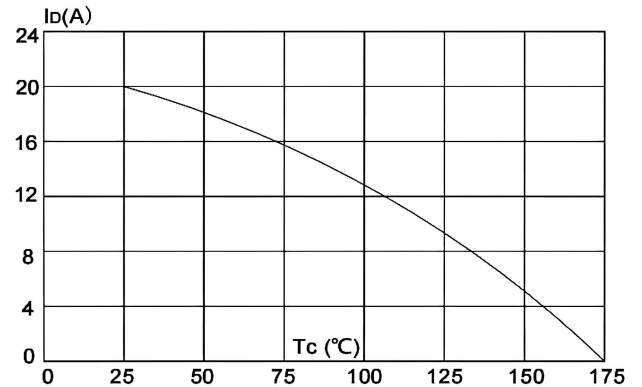
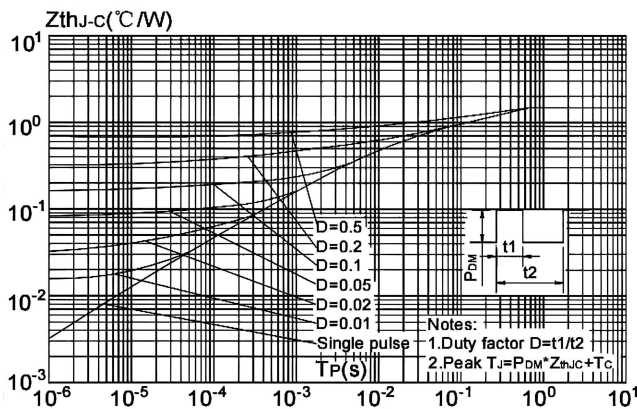
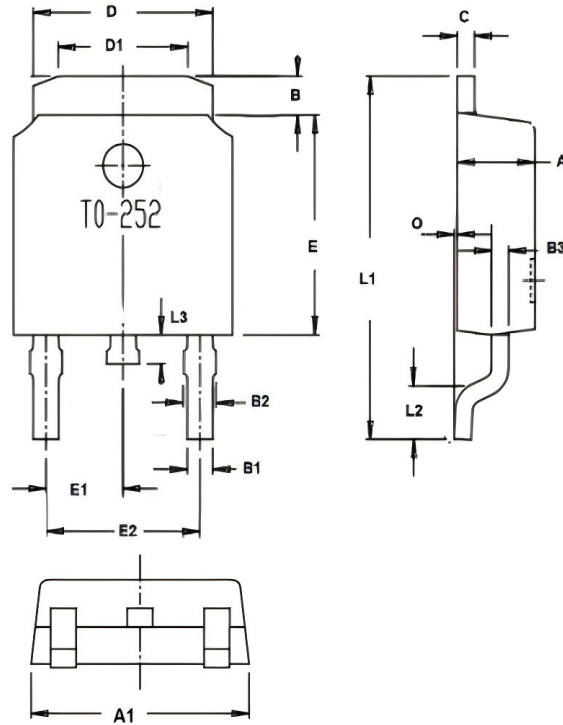


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



■ **Package Dimension 外形封装尺寸**



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.95	1.55
B1	0.6	0.8
B2	0.75	0.95
B3		
C	Typ0.5	
D	5.3	5.5
D1	3.65	4.05
E	5.8	6.4
E1	Typ2.3	
E2	Typ4.6	
O	0	0.15
L1	9	11
L2	Typ1.5	
L3	0.7	1
All Dimensions in millimeter		